

Diodes Incorporated for Discrete and Analog Semiconductors

QPAK/PPAP – 2140

Qualification Report

Manufacturer No.: PCN-2140 – Leadframe material change for SOT-25, SOT-26 and TSOT25 packages

Revision 0

Date: April 9, 2014

Qualified By: Diodes Incorporated

Also Applicable To: The part numbers listed in the associated PCN are Qualified by Similarity (QBS) to the devices included in this report.

Please go to www.diodes.com for current data sheets on the parts listed in this report.

Prepared By:	<u>Diodes US Document Control</u>	Date	<u>April 9, 2014</u>
Approved By:	<u>Diodes US QRA Department</u>	Date	<u>April 9, 2014</u>



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DIODES INCORPORATED

4949 Hedgcoxe Road, Suite # 200, Plano, TX 75024 USA
www.diodes.com



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DIODES INCORPORATED
4949 Hedgcoxe Road, Suite # 200
Plano, TX 75024 USA
(972) 987-3900
www.diodes.com



DATE: 9th April, 2014

PCN #: 2140

PCN Title: Leadframe material change for SOT-25, SOT-26 and TSOT25 packages

Dear Customer:

This is an announcement of change(s) to products that are currently being offered by Diodes Incorporated.

One of Diodes' tier-two suppliers of raw material for the manufacture of copper leadframes recently experienced a disaster resulting in plant closure. Having thoroughly reviewed all aspects of our supply chain and to assure continuity of supply to our customers we will be converting the leadframe material for devices packaged in SOT-25, SOT-26, and TSOT25 to CDA 194 alloy starting immediately as described in attached PCN form.

Please contact your local Diodes sales representative to acknowledge receipt of this PCN and for any sample requests.

Previously agreed upon customer specific change process requirements or device specific requirements will be addressed separately.

For questions or clarification regarding this PCN, please contact your local Diodes sales representative.

Sincerely,

Diodes Incorporated PCN Team



PRODUCT CHANGE NOTICE

PCN-2140 REV 00

Notification Date:	Implementation Date:	Product Family:	Change Type:	PCN #:
9 th April, 2014	Immediately	Analog and Discrete Semiconductors	Leadframe Material	2140
TITLE				
Leadframe material change for SOT-25, SOT-26 and TSOT25 packages				
DESCRIPTION OF CHANGE				
<p>One of Diodes' tier-two suppliers of raw material for the manufacture of copper leadframes recently experienced a disaster resulting in plant closure. Having thoroughly reviewed all aspects of our supply chain and to assure continuity of supply to our customers we will be converting the leadframe material for devices packaged in SOT-25, SOT-26, and TSOT25 at the Diodes SKE/DSH (Shanghai Kaihong Electronic Co./Diodes Inc. Shanghai) Assembly & Test Sites to CDA 194 alloy starting immediately. A separate product change notification will be issued for Hall effect sensors.</p> <p>Our currently qualified tier-one leadframe suppliers have already been manufacturing and supplying leadframes with CDA 194 alloy for a number of years. Furthermore, CDA 194 leadframes have already been used for select parts in above mentioned packages and extensively in other package types throughout Diodes.</p> <p>Full electrical characterization and high reliability testing has been completed using representative devices built with CDA 194 leadframes to ensure there is no change to device functionality or electrical specifications in the datasheet. Corresponding qualification data is available. There will be no change to the Form, Fit, or Function of products affected.</p>				
IMPACT				
Continuity of Supply.				
PRODUCTS AFFECTED				
See attached list.				
WEB LINKS				
Manufacturer's Notice:	http://www.diodes.com/quality/pcns			
For More Information Contact:	http://www.diodes.com/contacts			
Data Sheet:	http://www.diodes.com/products			
DISCLAIMER				
Unless a Diodes Incorporated Sales representative is contacted in writing upon receipt of this notice, all changes described in this announcement are considered approved.				

PCN-2140 Parts List

74AHC1G00W5-7	74LVC2G34W6-7	AP2171DWG-7	AP7312-1533W6-7	APX823-29W5G-7
74AHC1G02W5-7	74LVCE1G02W5-7	AP2171WG-7	AP7312-1828W6-7	APX823-31W5G-7
74AHC1G04W5-7	74LVCE1G04W5-7	AP2181DWG-7	AP7312-1830W6-7	APX823-40W5G-7
74AHC1G08W5-7	74LVCE1G08W5-7	AP2181WG-7	AP7312-1833W6-7	APX823-44W5G-7
74AHC1G09W5-7	74LVCE1G125W5-7	AP2191DWG-7	AP7312-3333W6-7	APX823-46W5G-7
74AHC1G125W5-7	74LVCE1G126W5-7	AP2191HWG-7	AP7331-10WG-7	APX824-23W5G-7
74AHC1G126W5-7	74LVCE1G32W5-7	AP2191WG-7	AP7331-12WG-7	APX824-26W5G-7
74AHC1G14W5-7	74LVCE1G86W5-7	AP2280-1WG-7	AP7331-15WG-7	APX824-29W5G-7
74AHC1G32W5-7	AL5801W6-7	AP2280-2WG-7	AP7331-18WG-7	APX824-31W5G-7
74AHC1G86W5-7	AL5801W6Q-7	AP2281-1WG-7	AP7331-20WG-7	APX824-40W5G-7
74AHC1GU04W5-7	AL5802-13	AP2281-3WG-7	AP7331-25WG-7	APX824-46W5G-7
74AHCT1G00W5-7	AL5802-7	AP2552AW6-7	AP7331-28WG-7	APX825A-26W6G-7
74AHCT1G02W5-7	AL8805W5-7	AP2552W6-7	AP7331-30WG-7	APX825A-29W6G-7
74AHCT1G08W5-7	AL8807W5-7	AP2553AW6-7	AP7331-33WG-7	APX825A-31W6G-7
74AHCT1G125W5-7	AL8808WT-7	AP2553W6-7	AP7331-WG-7	APX825A-44W6G-7
74AHCT1G126W5-7	AP131-18WG-7	AP331AWG-7	AP7332-1233W6-7	APX825A-46W6G-7
74AHCT1G14W5-7	AP131-25WG-7	AP331AWRG-7	AP7332-1828W6-7	AS431BKTR-G1
74AHCT1G32W5-7	AP131-25WL-7	AP431QL-7	AP7332-1833W6-7	ASMCC0164-7
74LVC1G00W5-7	AP131-28WG-7	AP432QL-7	AP7332-2833W6-7	ASMCC0195-7
74LVC1G02W5-7	AP131-30WL-7	AP5100WG-7	AP7332-3333W6-7	ASMCC0208-7
74LVC1G04W5-7	AP131-33WG-7	AP5724WG-7	AP7335-10WG-7	ASMCC0209-7
74LVC1G06W5-7	AP131-33WL-7	AP5725WG-7	AP7335-12WG-7	AT1042K6-5.0TRG1
74LVC1G07W5-7	AP133-WG-7	AP5726WG-7	AP7335-18WG-7	AT2042K6-5.0TRG1
74LVC1G08W5-7	AP139-15WL-7	AP5727WG-7	AP7335-25WG-7	AZ431LAKTR-E1
74LVC1G10W6-7	AP139-18WG-7	AP7115-10WG-7	AP7335-27WG-7	AZ431LBKTR-E1
74LVC1G11W6-7	AP139-25WG-7	AP7115-12WG-7	AP7335-28WG-7	BAS21TM-7
74LVC1G125W5-7	AP139-30WG-7	AP7115-15WG-7	AP7335-33WG-7	D1213A-02SM-7
74LVC1G126W5-7	AP139-30WL-7	AP7115-18WG-7	AP7335-39WG-7	D1213A-02SO-7
74LVC1G14W5-7	AP139-33WG-7	AP7115-25WG-7	AP7335A-50W-7	D1213A-04SO-7
74LVC1G17W5-7	AP139-33WL-7	AP7115-28WG-7	AP7335-WG-7	D5V0F4U6SO-7
74LVC1G32W5-7	AP1522WA	AP7115-30WG-7	AP7365-10WG-7	D5V0L4B5SO-7
74LVC1G57W6-7	AP1603WL-7	AP7115-33WG-7	AP7365-12WG-7	D5V0L4B5TS-7
74LVC1G58W6-7	AP2125K-1.8TRG1	AP7115-35WG-7	AP7365-18WG-7	DCX114YK-7
74LVC1G86W5-7	AP2125K-2.5TRG1	AP7311-12WG-7	AP7365-25WG-7	DCX114YK-7-F
74LVC1G97W6-7	AP2125K-2.8TRG1	AP7311-15WG-7	AP7365-28WG-7	DCX124EK-7
74LVC1G98W6-7	AP2125K-3.3TRG1	AP7311-18WG-7	AP7365-30WG-7	DCX124EK-7-F
74LVC2G04W6-7	AP2141DWG-7	AP7311-25WG-7	AP7365-33WG-7	DCX144EK-7
74LVC2G06W6-7	AP2141WG-7	AP7311-33WG-7	AP7365-WG-7	DDC123JK-7-F
74LVC2G07W6-7	AP2151DWG-7	AP7311-WG-7	AP8800AWT-7	DIMD10A-7
74LVC2G14W6-7	AP2151WG-7	AP7312-1218W6-7	APX321WG-7	DMC2700UDM-7
74LVC2G17W6-7	AP2161DWG-7	AP7312-1233W6-7	APX823-23W5G-7	DMG6402LDM-7



DMG9926UDM-7	TLV431AE5TA	ZXMN10A08E6TA	ZXTC2045E6TA
DMMT2907A-7	TLV431BE5TA	ZXMN10B08E6QTA	ZXTC2061E6TA
DMMT3906-7-F	ZHCS2000TA	ZXMN10B08E6TA	ZXTC2062E6TA
DMMT5401-7-F	ZLLS2000TA	ZXMN2088DE6TA	ZXTC2063E6TA
DMMT5551-7-F	ZTD09N50DE6QTA	ZXMN2A01E6TA	ZXTD09N50DE6TA
DMMT5551S-7-F	ZVN4525E6TA	ZXMN2A03E6TA	ZXTD2090E6TA
DMN2004DMK-7	ZVP4525E6TA	ZXMN2B03E6TA	ZXTD4591E6TA
DMN2100UDM-7	ZX5T2E6TA	ZXMN3A01E6TA	ZXTD6717E6QTA
DMN2215UDM-7	ZXCL280E5TA	ZXMN3A03E6TA	ZXTD6717E6TA
DMN3033LDM-7	ZXCL300E5TA	ZXMN6A08E6QTA	ZXTP2006E6TA
DMN3051LDM-7	ZXCL330E5TA	ZXMN6A08E6TA	
DMN3115UDM-7	ZXCT1010E5TA	ZXMP10A17E6QTA	
DMN3115UDMQ-7	ZXCT1011E5TA	ZXMP10A17E6TA	
DMN5L06DMK-7	ZXCT1012ET5TA	ZXMP2120E5TA	
DMN601DMK-7	ZXCT1020E5TA	ZXMP3A17E6TA	
DMP2066LDM-7	ZXCT1021E5TA	ZXMP4A57E6TA	
DMP2130LDM-7	ZXCT1022E5TA	ZXMP6A17E6QTA	
DMP2240UDM-7	ZXCT1041E5TA	ZXMP6A17E6TA	
DMP3056LDM-7	ZXCT1050E5TA	ZXRE060AET5TA	
DMP3098LDM-7	ZXCT1051E5TA	ZXRE060ET5TA	
DRDC3105E6-7	ZXCT1080E5TA	ZXRE160AET5TA	
DSS4160DS-7	ZXCT1081E5TA	ZXRE160ET5TA	
DT1042-04SO-7	ZXCT1082E5TA	ZXRE250AW5-7	
DT2042-04SO-7	ZXCT1083E5TA	ZXSC300E5TA	
DVRN6056-7-F	ZXCT1084E5TA	ZXSC310E5TA	
DVRN6056-7-G	ZXCT1085E5TA	ZXSC400E6TA	
IMT17-7	ZXCT1086E5TA	ZXSC410E6TA	
IMX8-7-F	ZXCT1087E5TA	ZXSC420E6TA	
LMN200B01-7	ZXCT1110W5-7	ZXT10N15DE6TA	
LMV321WG-7	ZXGD3001E6TA	ZXT10N20DE6TA	
MMBD3004BRM-7-F	ZXGD3002E6TA	ZXT10N50DE6TA	
MMBD4448HTM-7-F	ZXGD3003E6TA	ZXT10P12DE6TA	
MMBD5004BRM-7	ZXGD3004E6TA	ZXT10P20DE6TA	
MMDT2227M-7	ZXGD3005E6TA	ZXT10P20DE6TC	
MMDTA06-7	ZXGD3006E6QTA	ZXT10P40DE6TA	
MMDTA42-7-F	ZXGD3006E6TA	ZXT13N15DE6TA	
SD103ASDM-7-F	ZXLD1350ET5TA	ZXT13N20DE6TA	
SDM03MT40-7-F	ZXLD1615ET5TA	ZXT13N50DE6TA	
SDM03MT40A-7-F	ZXM62N02E6TA	ZXT13P12DE6TA	
SDM10M45SD-7-F	ZXM62P02E6TA	ZXT13P20DE6TA	
TL431AW5-7	ZXM62P03E6TA	ZXT13P40DE6TA	
TL431BW5-7	ZXMN10A08E6QTA	ZXTC2045E6QTA	

Certificate of Design, Construction & Qualification



Description: Qual package SOT-26 material change from E64 to CDA194

	Part Number	
	Package	
	Package Size	
	Die Name(s)	
	Wafer FAB	
	Wafer Diameter	
	Bond Type (at Die)	
	Bond Type (at LF)	
	No. of bond over active area	
	Lead Material Manufacture	
	Max Junction Temp	
	Max Thermal resistance Junc (case)	
	Max Thermal resistance Junc (amibent)	
	Front Metal Type	
	Die passivation thickness range	
	Die Size (W/L/Thickness)	
	Die Process / Technology	
	Die Quantity (eg. Die per package)	
	DB Epoxy/Solder Type	
	Die Attach Material	
	Wire Bond Material (Au, Cu, Al)	
	Wire Diameter	
	Front Metal Thickness	
	Leadframe Type	
	Leadframe Material	
	Molding Compound Type	
	Green Compound (Yes/No)	
	Lead-Free (Yes/No)	
	Assembly Site	
	Test Site	
	DataSheet	

Qual Device 1
74LVC2G07W6-7
SOT-26
3.0*2.8*1.15
AW06010286A0-007-CN
DHC
6"
Ball
Wedge
6
NBKQ
N/A
52C/W
204C/W
AlCu
Oxide 4kA SiN 6kA
0.539*0.35*0.205
CMOS 5V, 0.5um, 1P3M
1
Epoxy
84-1LMISR4
Au
Au 0.7mil
2um
SOT-26A
CDA194
EME-G700
Yes
Yes
DSH
DSH
74LVC2G07

Qual Device 2
ZXSC400E6TA
SOT-26
3.0*2.8*1.15
ZXSC400F
OFAB
6"
Ball
Wedge
6
NBKQ
N/A
N/A
N/A
N/A
N/A
Ox/ Nitride
1.422*0.762
N/A
1
Epoxy
8200TI
Au
Au 1.0mil
1.2um
SOT-26A
CDA194
CEL-1702HF9 SK
Yes
Yes
DSH
DSH
ZXSC400

Realibility Testing

Test	Test Conditions	Duration / Limits	Fail/SS	X = Test Needed	Results Pass/Fail	X = Test Needed	Results Pass/Fail
MSL1 Pre-cond	Bake 125C	24 Hrs	0/154	X	Pass	X	Pass
	Soak 85C, 85% RH	168Hrs	0/154	X	Pass	X	Pass
	IR reflow 260C	3 cycles	0/154	X	Pass	X	Pass
HAST	130C, 85%RH 33.3 psia 100% Bias	96 Hrs	0/77	X	Pass	X	Pass
HTSL	150C	168 Hrs	0/77	X	Pass	X	Pass
Die Shear	MIL-STD-750 (2017)	Cpk>1.66	0/30	X	Pass	X	Pass
WBP	MIL-STD883-2011	Cpk>1.66	0/30	X	Pass	X	Pass
PD	JESD22-B100B	Package Outline	0/30	X	Pass	X	Pass
Solderability	245C +0/5C	5 Seconds	0/10	X	Pass	X	Pass

Remark:

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Summary:
Submitted By:
Approved By:

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Certificate of Design, Construction & Qualification



Description: TSOT23-5 A LDF material change qual

				Qual Device 1		Qual Device 2	
	Part Number			AL8808WT-7		ZXLD1615ET5TA	
	Package			TSOT23-5		TSOT23-5	
	Package Size (mm)			2.8*2.9*0.92		2.8*2.9*0.92	
	Die Name(s)			AL8808N		ZXLD1615F	
	Wafer FAB			ZETEX		OFAB	
	Wafer Diameter			8"		6"	
	Bond Type (at Die)			Ball		Ball	
	Bond Type (at LF)			Wedge		Wedge	
	No. of bond over active area			8		8	
	Lead Material Manufacture			ASM		ASM	
	Header plating (Die Land Area)			Ag 3~8um		Ag 3~8um	
	Max Junction Temp			150°C/W		150°C/W	
	Front Metal Type			TIN/ Al(0.5% Cu)/ TIN		TIN/ Al(0.5% Cu)/ TIN	
	No of masks Steps			24		24	
	Die Size (W/L/Thickness)			0.9*1.03		1.575* 0.885	
	Die Quantity (eg. Die per package)			1		1	
	DB Epoxy/Solder Type			Epoxy		Epoxy	
	Die Attach Material			8200TI		8200TI	
	Wire Bond Material (Au, Cu, Al)			Cu		Au	
	Wire Diameter			0.8mil		1.0mil	
	Leadframe Type			TSOT23-5 A		TSOT23-5 A	
	Leadframe Material			CDA194		CDA194	
	Molding Compound Type			CEL-1702HF9 SK		CEL-1702HF9 SK	
	Green Compound (Yes/No)			Yes		Yes	
	Lead-Free (Yes/No)			Yes		Yes	
	Assembly Site			SAT		SAT	
	Test Site			SAT		SAT	
	DataSheet			AL8808		ZXLD1615	
	Realibility Testing						
Test	Test Conditions	Duration / Limits	Fail/SS	X = Test Needed		QBS Test Completed	Results Pass/Fail
MSL1 Pre-cond	Bake 125C	24 Hrs	0/154	X	Pass	X	Pass
	Soak 85C, 85% RH	168Hrs	0/154	X	Pass	X	Pass
	IR reflow 260C	3 cycles	0/154	X	Pass	X	Pass
TC HAST	-65C-150C	500 cycles	0/77	X	Pass	X	
	130C, 85%RH 33.3 psia 100% Bias	96 Hrs	0/77	X	Pass	X	
HTSL	150C	168 Hrs	0/77	X	Pass	X	Pass
		500 Hrs	0/77	X	Pass	X	
WBP	MIL-STD883-2011	Cpk>1.66	0/30	X	Pass	X	Pass
WBS	JESD22-B116B	Cpk>1.66	0/30	X	Pass	X	Pass
PD	JESD22-B100B	Package Outline	0/30	X	Pass	X	Pass
Remark:							
Summary: _____ Submitted By: _____ Approved By: _____							

Certificate of Design, Construction & Qualification



Description: Package SOT-25 material change from EFTEC-64T to CDA194

				Qual Device 1	
	Part Number			AP2125K-3.3TRG1	
	Package			SOT-25	
	Package Size			3.0*2.8*1.15	
	Die Name(s)			AW011-001	
	Wafer FAB			BCD	
	Wafer Diameter			6"	
	Bond Type (at Die)			Ball	
	Bond Type (at LF)			Wedge	
	No. of bond over active area			5	
	Lead Material Manufacture			NBKQ/ASM	
	Front Metal Type			0.8umAL+560ATIN	
	Die Size (W/L/Thickness)			0.7*0.67mm	
	Die Process / Technology			0.5um CMOS	
	Die Quantity (eg. Die per package)			1	
	DB Epoxy/Solder Type			Epoxy	
	Die Attach Material			8200TI	
	Wire Bond Material (Au, Cu, Al)			Cu	
	Wire Diameter			1.0mil	
	Front Metal Thickness			0.8umAL+560ATIN	
	Leadframe Type			SOT-25 H	
	Leadframe Material			CDA194	
	Molding Compound Type			CEL-1700HF40SK-D3	
	Green Compound (Yes/No)			Yes	
	Lead-Free (Yes/No)			Yes	
	Assembly Site			SAT	
	Test Site			SAT	
	DataSheet			AP2125	
Reliability Testing					
Test	Test Conditions	Duration / Limits	Fail/SS	X = Test Needed	Pass/Fail
MSL3 Pre-cond	Bake 125C	24 Hrs	0/154	X	Pass
	Soak 30C, 60% RH	192Hrs	0/154	X	Pass
	IR reflow 260C	3 cycles	0/154	X	Pass
TC	-65C-150C	500 cycles	0/77	X	Pass
		1000 cycles	0/77	X	Pass
UHASt	130C, 85%RH 33.3 psia	96 Hrs	0/77	X	Pass
HTSL	150C	168 Hrs	0/77	X	Pass
		500 Hrs	0/77	X	Pass
		1000 Hrs	0/77	X	Pass
Die Shear	MIL-STD-750 (2017)	Cpk>1.66	0/30	X	Pass
WBP	MIL-STD883-2011	Cpk>1.66	0/30	X	Pass
WBS	JESD22-B116B	Cpk>1.66	0/30	X	Pass
Remark:					
Summary: _____					
Submitted By: _____					
Approved By: _____					



CERTIFICATE OF DESIGN AND CONSTRUCTION

Printed specifications are not controlled documents. Verify revision before using.

Assembly and Test Site	DIODES INC	Glass Transition Temperature (T_G)	N/A
DIC P/N	SDM03MT40-7-F	Lead Frame Type	SOT-26 G
Package Type	SOT-26	Lead Frame Manufacturer	NBKQ
DIE P/N	YHF014	Lead Frame Material	CDA194
Die Line or Process	SBR	Terminal Finish (Plating) Material	N/A
Wafer Diameter	5 inch	Header Plating (Die Land Area)	Silver Spot Plate
Wafer Fab Site(s)	PHENITEC	Max Junction Temperature (T_j)	125° C
ID Method (multiple sites)	N/A	Max Thermal Resistance Junction to Case (θ_{JC})	N/A
Assembly Locations(s)	Shanghai Kaihong Electronic Co., Ltd. No.999 Chenchun Road, Xinqiao Town, Songjiang, Shanghai, P.R. China 201612 DIODES INC. IN SHANGHAI, Plant1, NO.111-10 Songjiang Export Processing Zone, Shanghai, P.R. China 201600	Max Thermal Resistance Junction to Ambient (θ_{JA})*	N/A
Test Locations(s)	DIODES INC. IN SHANGHAI, Plant1, NO.111-10 Songjiang Export Processing Zone, Shanghai, P.R. China 201600	Front Metal Type (Top Layer)	N/A
Die attach Method / Material	Epoxy/9005SP	Front Metal Thickness (Top Layer)	N/A
Bond Wire/Clip Material & Wire Diameter	Au wire, 1.0mil	Back Metal Type (All Layers)	N/A
Bond Type (at top side of the die)	N/A	Back Metal Thickness (all Layers)	N/A
Bond Type (at leadframe)	N/A	Die Conformal Coating (Passivation)	N/A
No. of Bonds over Active Area	3	Die Passivation Thickness Range	N/A
Mold Compound Material Type	CEL-1702HF9 SK	Die Size (Width x Length x Thickness) in mm	0.23*0.23
Mold Compound Material Manufacturer	HITACHI	No. of Mask Steps	

Completed by		Date	Certified by	Date
Typed/Printed				
Signature				
Title			Discrete Manager	



SHANGHAI KAIHONG ELECTRONIC CO.,LTD

Reliability Test Summary Report

FACTORY:		PART NUMBER :SDM03MT40-7 SWR1311059 CUSTOMER				
		Package:SOT26		DIODES INC.:		
LABORATORY (If Different):		PART DESCRIPTION:Urgent material change-SOT-26G qual(NBKQ),(wafer:YHF014)				
DW-008 (AEC Q101) Test#	Test Description	Test Conditions	#Lots	#To Test	Results	REMARKS
7.3.2 (1)	PRE- AND POST- STRESS ELECTRICAL TEST (TEST)	Per Spec				
7.3.3 (2)	PRECONDITIONING (PC)	JESD22 A-113 N/A for Axial	1	308	0/308	
7.3.5.1 (3)	EXTERNAL VISUAL (EV)	MIL-STD-750 METHOD 2071	1	500	0/500	
7.3.5.2 (4)	PARAMETRIC VERIFICATION (PV)	Per Data Sheet Ta1=-55°C, Ta2=25°C, Ta3=85°C, Ta4=150°C Characteristic VZ@IZT=5mA Characteristic IR@VR=5V Characteristic VF@IF=10mA	1 of 3	25		
	Lot #2		2 of 3	25		
	Lot #3		3 of 3	25		
7.3.5.3	FORWARD SURGE	MIL-750D, Method 4066	1	45		
7.3.5.4 (5)	HIGH TEMP. REVERSE BIAS (HTRB)	T=125°C Vr=32V, PER JESD22 A-108	1	77		
	Pretest		1	77		
	@ 500 Hours	T=125°C Vr=32V, PER JESD22 A-108	1	77		
	Final 1000Hours	T=125°C Vr=32V, PER JESD22 A-108	1	77		
(6)	HIGH TEMP GATE BIAS (HTGB)	MIL-750D, Method 4066			N/A	
7.3.5.5 (7)	TEMPERATURE CYCLING (TC)	T=-65°C-150°C, PER JESD22 A-104				
	Pretest		1	77	0/77	
	@ 500 Cycles	T=-65°C-150°C, PER JESD22 A-104	1	77	0/77	
	Final 1000 Cycles	T=-65°C-150°C, PER JESD22 A-104	1	77	0/77	
7.3.5.6 (8)	AUTOCLAVE (AC)	T=121°C 15PSIG 100%RH	1	77	0/77	
7.3.5.7 (9)	H3TRB	T=85°C RH=85% VR=32v	1	77		
	Pretest		1	77	0/77	
	@ 500 Hours	T=85°C RH=85% VR=32v	1	77	0/77	
	Final 1000Hours	T=85°C RH=85% VR=32v	1	77	0/77	
7.3.5.7 (9a)	HAST	T=131°C 85%RH Vr=32V	1	77	0/77	
7.3.5.8 (10)	INTERMITTENTOPERATING LIFE (IOL)	IF=30mA, PER MIL-STD-750 METHOD 1037				15000cy @2min on/off
	Pretest	MIL-STD-750 METHOD 1037	1	77	0/77	
	Midpoint 7560CY	MIL-STD-750 METHOD 1037	1	77	0/77	
	After 15000CY	MIL-STD-750 METHOD 1037	1	77	0/77	
(10a)	POWER AND TEMP. CYCLE (PTC)	JESD22 A-105, Per Table AEC-Q101, p11	1	77		
(Optional)	Pretest	JESD22 A-105, Per Table AEC-Q101, p11	1	77		
	Midpoint	JESD22 A-105, Per Table AEC-Q101, p11	1	77		
	After	JESD22 A-105, Per Table AEC-Q101, p11	1	77		
7.3.5.9 (11)	ESD CHARACTERIZATION (ESD)	PER AEC-Q101-001 & -002	1	60		
7.3.5.10 (12)	D.P.A. (DPA)	AEC Q101-004 SEC. 4	1	2	0/2	
7.3.5.11 (13)	PHYSICAL DIMENSION (PD)	PER JESD22 B-100	1	30	0/30	
7.3.5.12 (14)	TERMINAL STRENGTH (TS)	MIL-STD-750, Method 2036	1	30		
7.3.5.13 (15)	RESISTANCE TO SOLVENTS (RTS)	JESD22 B-107	1	30		
(16)	CONSTANT ACCELERATION (CA)	N/A, not hermetically sealed device.	N/A	N/A		
(17)	VIBRATION VARIABLE FREQUENCY (VVF)	N/A, not hermetically sealed device.	N/A	N/A		
7.3.5.14 (20)	RESISTANCE TO SOLDER HEAT (RSH)	JESD22 B-106	1	30	0/30	260°C @30S
7.3.5.15 (21)	SOLDERABILITY (SD)	J-STD-002	1	10	0/10	245°C @5S
7.3.5.16 (22)	THERMAL RESISTANCE (TR)	JESD 24-3, 24-4, 24-6 as appropriate	1	10	0/10	
7.3.5.17 (23)	WIRE BOND STRENGTH (WBS)	MIL-STD-750 METHOD 2037	1	30		
7.3.5.18 (24)	BOND SHEAR (BS)	AEC-Q101-003	1	30		
7.3.5.19 (25)	DIE SHEAR (DS)	MIL-STD-750 METHOD 2017	1	30	0/30	
Summary:	The lot passed 1000hrs full hi-rel test.					
Submitted by:	Joan Yu 02/10/14	Approved by:Adam Gu 02/10/14				



CERTIFICATE OF DESIGN AND CONSTRUCTION

Printed specifications are not controlled documents. Verify revision before using.

Assembly and Test Site	DIODES INC	Glass Transition Temperature (T_G)	N/A
DIC P/N	ZXMP4A57E6QTA	Lead Frame Type	SOT-26 C
Package Type	SOT-26	Lead Frame Manufacturer	NBKQ
DIE P/N	ZXMP4A57D	Lead Frame Material	CDA194
Die Line or Process	SBR	Terminal Finish (Plating) Material	N/A
Wafer Diameter	6 inch	Header Plating (Die Land Area)	Silver Spot Plate
Wafer Fab Site(s)	OFAB	Max Junction Temperature (T_j)	150° C
ID Method (multiple sites)	N/A	Max Thermal Resistance Junction to Case (θ_{JC})	N/A
Assembly Locations(s)	Shanghai Kaihong Electronic Co., Ltd. No.999 Chenchun Road, Xinqiao Town, Songjiang, Shanghai, P.R. China 201612 DIODES INC. IN SHANGHAI, Plant1, NO.111-10 Songjiang Export Processing Zone, Shanghai, P.R. China 201600	Max Thermal Resistance Junction to Ambient (θ_{JA})*	N/A
Test Locations(s)	DIODES INC. IN SHANGHAI, Plant1, NO.111-10 Songjiang Export Processing Zone, Shanghai, P.R. China 201600	Front Metal Type (Top Layer)	N/A
Die attach Method / Material	Epoxy/9005SP	Front Metal Thickness (Top Layer)	N/A
Bond Wire/Clip Material & Wire Diameter	Cu wire, 1.7mil	Back Metal Type (All Layers)	N/A
Bond Type (at top side of the die)	N/A	Back Metal Thickness (all Layers)	N/A
Bond Type (at leadframe)	N/A	Die Conformal Coating (Passivation)	N/A
No. of Bonds over Active Area	3	Die Passivation Thickness Range	N/A
Mold Compound Material Type	CEL-1702HF9 SK	Die Size (Width x Length x Thickness) in mm	1.85*1.09
Mold Compound Material Manufacturer	HITACHI	No. of Mask Steps	

Completed by		Date	Certified by	Date
Typed/Printed				
Signature				
Title			Discrete Manager	



Reliability Test Summary

FACTORY:		PART NUMBER : ZXMP4A57E6QTA SWR1311063		CUSTOMER:		
		Package Description : SOT-26		DIODES INC.:		
LABORATORY (If Different):		PART DESCRIPTION : Qualification for SOT-26 C NBKQ LDF(ZXMP4A57D, 1.7mil Cu Wire + CEL-1702HF9 SK).				
DW-008 (AEC Q101) Test#	Test Description	Test Conditions	#Lots	#To Test	Results	REMARKS
7.3.2 (1)	PRE- AND POST- STRESS ELECTRICAL TEST (TEST)	Per Spec				
7.3.3 (2)	PRECONDITIONING (PC)	JESD22 A-113 N/A for Axial	1	308	0/308	
7.3.5.1 (3)	EXTERNAL VISUAL (EV)	MIL-STD-750 METHOD 2071	1	500	0/500	
7.3.5.2 (4)	PARAMETRIC VERIFICATION (PV)	Per Data Sheet Ta1=-55°C, Ta2=25°C, Ta3=85°C, Ta4=150°C Characteristic BV _{DSS} @VGS=0V, ID=-250uA Characteristic IDSS@VDS=-40V, VGS=0V Characteristic IGSS@VGS=±20V, VDS=0V Characteristic VGS(th)@VDS=VGS, ID=-250uA Characteristic RDSON@VGS=-10V, ID=-4A Characteristic RDSON@VGS=-4.5V, ID=-2A Characteristic yFS@VDS=-15V, ID=-4A Characteristic VSD@VGS=0V, ID=-4A	1 of 3	25	N/A	
	Lot #2		2 of 3	25	N/A	
	Lot #3		3 of 3	25	N/A	
7.3.5.3	FORWARD SURGE	MIL-750D, Method 4066	1	45	N/A	
7.3.5.4 (5)	HIGH TEMP. REVERSE BIAS (HTRB)	T=150°C Vd=32V, PER JESD22 A-108	1	77	N/A	
(6)	HIGH TEMP GATE BIAS (HTGB)	T=150°C Vg=20V, PER JESD22 A-108	1	77	N/A	
7.3.5.5 (7)	TEMPERATURE CYCLING (TC)	T=-65°C-150°C, PER JESD22 A-104				
	Pretest		1	77	0/77	
	@ 500 Cycles	T=-65°C-150°C, PER JESD22 A-104	1	77	0/77	
	Final 1000 Cycles	T=-65°C-150°C, PER JESD22 A-104	1	77	0/77	
7.3.5.6 (8)	AUTOCLAVE (AC)	T=121°C 15PSIG 100%RH				
	Pretest		1	77	0/77	
	Final 96 Hours	T=121°C 15PSIG 100%RH	1	77	0/77	
7.3.5.7 (9-1)	Highly Accelerated Stress Test(HAST)	T=130°C RH=85% Vd=32V				
	Pretest		1	77	0/77	
	Final 96 Hours	T=130°C RH=85% Vd=32V	1	77	0/77	
7.3.5.7 (9-2)	High Humidity High Temp. Reverse Bias(H ³ TRB)	T=85°C RH=85% Vd=32V	1	77	N/A	No request if HAST passed
7.3.5.8 (10)	INTERMITTENT OPERATING LIFE (IOL)	Vd=5V / Id=200mA; PER MIL-STD-750 METHOD 1037				
	Pretest		1	77	0/77	
	@ 7560 Cycles	MIL-STD-750 METHOD 1037	1	77	0/77	
	Final 15000 Cycles	MIL-STD-750 METHOD 1037	1	77	0/77	
(10a)	POWER AND TEMP. CYCLE (PTC)	JESD22 A-105, Per Table AEC-Q101, p11	1	77	N/A	
7.3.5.9 (11)	ESD CHARACTERIZATION (ESD)	PER AEC-Q101-001 & -002	1	60	N/A	
7.3.5.10 (12)	D.P.A. (DPA)	AEC Q101-004 SEC. 4	1	4	N/A	
7.3.5.11 (13)	PHYSICAL DIMENSION (PD)	PER JESD22 B-100	1	30	0/30	
7.3.5.12 (14)	TERMINAL STRENGTH (TS)	MIL-STD-750, Method 2036	1	30	N/A	
7.3.5.13 (15)	RESISTANCE TO SOLVENTS (RTS)	JESD22 B-107	1	30	N/A	
(16)	CONSTANT ACCELERATION (CA)	N/A, not hermetically sealed device.	N/A	N/A		
(17)	VIBRATION VARIABLE FREQUENCY (VVF)	N/A, not hermetically sealed device.	N/A	N/A		
(18)	MECHANICAL SHOCK (MS)	N/A, not hermetically sealed device.	N/A	N/A		
(19)	HERMETICITY (HER)	N/A, not hermetically sealed device.	N/A	N/A		
7.3.5.14 (20)	RESISTANCE TO SOLDER HEAT (RSH)	JESD22 B-106	1	30	0/30	260°C @30sec
7.3.5.15 (21)	SOLDERABILITY (SD)	J-STD-002	1	10	0/10	245°C @5sec
7.3.5.16 (22)	THERMAL RESISTANCE (TR)	JESD 24-3, 24-4, 24-6 as appropriate	1	10	0/10	
7.3.5.17 (23)	WIRE BOND STRENGTH (WBS)	MIL-STD-750 METHOD 2037	1	25	N/A	
7.3.5.18 (24)	BOND SHEAR (BS)	AEC-Q101-003	1	25	N/A	
7.3.5.19 (25)	DIE SHEAR (DS)	MIL-STD-750 METHOD 2017	1	30	0/30	
(26)	UNCLAMPED INDUCTIVE SWITCHING (UIS)	N/A, not for Diode	N/A	N/A		
(27)	DIELECTRIC INTEGRITY (DI)	N/A, not for Diode	N/A	N/A		
Summary: The lot passed the precondition test and 1000hrs hi-rel tests.						
Submitted by: Jianhua Yang 2/14/14		Approved by: Adam Gu 2/14/14				